

제22회 한국반도체학술대회

2015년 2월 10일(화) - 12일(목), 인천 송도컨벤시아

A. Interconnect & Package 분과

Room A
1F / 104호

2015년 2월 12일(목) 14:50-16:20

[TA3-A] Conductors, Contacts and Low-k Dielectrics

좌장: 이원준 (세종대학교), 안상훈 (삼성전자)

- | | | |
|---------|-------------|---|
| TA3-A-1 | 14:50-15:05 | Electromigration Reliability of Silver Interconnect Fabricated by Reverse Offset Printing
Jae-Seon Hwang ¹ , Na-Rae Kim ¹ , Jae-Chan Lee ¹ , and Young-Chang Joo ^{1,2}
¹ Department of Materials Science & Engineering, Seoul National University,
² Research Institute of Advanced Materials (RIAM), Seoul National University |
| TA3-A-2 | 15:05-15:20 | Interconnect Filling Improvement by Reduction of CuOx before Electroplating
Tighe A. Spurlin and Jonathan Reid
Lam Research Corporation |
| TA3-A-3 | 15:20-15:35 | 메모리 소자용 금속배선의 배선간 접합 변화가 일렉트로마이그레이션 신뢰성에 미치는 영향
장경태 ¹ , 박용진 ¹ , 정민우 ¹ , 임승민 ¹ , 연한울 ¹ , 조주영 ¹ , 신진섭 ² , 우병욱 ² , 배장용 ² , 황유철 ² , 주영창 ¹
¹ 재료공학부, 서울대학교, ² 개발QA팀, 삼성전자 |
| TA3-A-4 | 15:35-15:50 | The effects on the formation process and Schottky Barrier Height of Ytterbium Silicide by Alloying with Molybdenum
Sekwon Na, Jun-gu Kang, Juyun Choi, Hyoungsub Kim, and Hoo-Jeong Lee
School of Advanced Materials Science and Engineering, Sungkyunkwan University |
| TA3-A-5 | 15:50-16:05 | Schottky Barrier Engineering in Ti/TiO₂ Metal-Insulator-Silicon Contact
Ryuji Tomita, Joongon lee, Kuo Tai Huang, Chulsung Kim, Sangjin Hyun, and Jahum Ku
Semiconductor R&D Center, Samsung Electronics Co. Ltd. |
| TA3-A-6 | 16:05-16:20 | Improvement in Mechanical Properties and Reliability of Porous Low-k through Novel UV Cure Process
Jong Min Baek, Woo Kyung Yu, Seung Wook Choi, Seung Hyuk Choi, Kyu Hee Han, Ok Hee Park, Tae-Jin Yim, Keeyoung Jun, Sang Hoon Ahn, Byung Hee Kim, Nae-In Lee, Ja-Hum Ku, Ho-Kyu Kang, and ES Jung
Semiconductor R&D Center Process Development Team, Samsung Electronics Co., Ltd. |